

MM54HC251/MM74HC251 8-Channel TRI-STATE® Multiplexer

General Description

This 8-channel digital multiplexer with TRI-STATE outputs utilizes advanced silicon-gate CMOS technology. Along with the high noise immunity and low power consumption of standard CMOS integrated circuits, it possesses the ability to drive 10 LS-TTL loads. The large output drive capability and TRI-STATE feature make this part ideally suited for interfacing with bus lines in a bus oriented system.

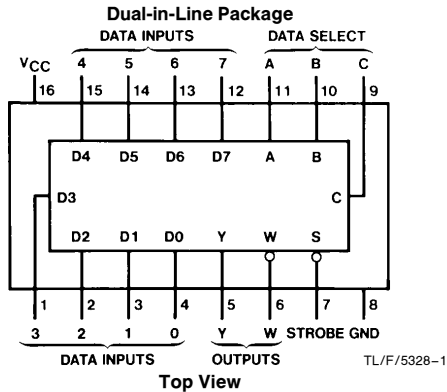
This multiplexer features both true (Y) and complement (W) outputs as well as a STROBE input. The STROBE must be at a low logic level to enable this device. When the STROBE input is high, both outputs are in the high impedance state. When enabled, address information on the data select inputs determines which data input is routed to the Y and W

outputs. The 54HC/74HC logic family is speed, function, as well as pinout compatible with the standard 54LS/74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Typical propagation delay
Data select to Y: 26 ns
- Wide supply range: 2–6V
- Low power supply quiescent current: 80 μ A maximum (74HC)
- TRI-STATE outputs for interface to bus oriented systems

Connection and Logic Diagrams

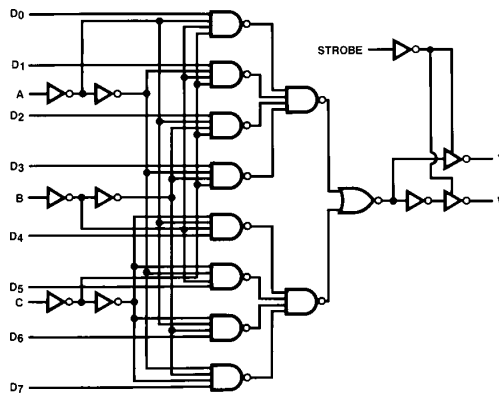


Order Number MM54HC251 or MM74HC251

Truth Table

Inputs			Outputs		
Select			Strobe S	Y	W
C	B	A			
X	X	X	H	Z	Z
L	L	L	L	D0	$\overline{D0}$
L	L	H	L	D1	$\overline{D1}$
L	H	L	L	D2	$\overline{D2}$
L	H	H	L	D3	$\overline{D3}$
H	L	L	L	D4	$\overline{D4}$
H	L	H	L	D5	$\overline{D5}$
H	H	L	L	D6	$\overline{D6}$
H	H	H	L	D7	$\overline{D7}$

H = high logic level, L = logic level
 X = irrelevant, Z = high impedance (off)
 D0, D1 . . . D7 = the level of the respective D input



TL/F/5328-2

TRI-STATE® is a registered trademark of National Semiconductor Corp.

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	-0.5 to +7.0V
DC Input Voltage (V_{IN})	-1.5 to $V_{CC} + 1.5V$
DC Output Voltage (V_{OUT})	-0.5 to $V_{CC} + 0.5V$
Clamp Diode Current (I_{IK}, I_{OK})	± 20 mA
DC Output Current, per pin (I_{OUT})	± 25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	± 50 mA
Storage Temperature Range (T_{STG})	-65°C to +150°C
Power Dissipation (P_D) (Note 3)	600 mW
S.O. Package only	500 mW
Lead Temp. (T_L) (Soldering 10 seconds)	260°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temp. Range (T_A)			
MM74HC	-40	+85	°C
MM54HC	-55	+125	°C
Input Rise or Fall Times (t_r, t_f)			
$V_{CC} = 2.0V$		1000	ns
$V_{CC} = 4.5V$		500	ns
$V_{CC} = 6.0V$		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V_{CC}	$T_A = 25^\circ C$			Units							
				74HC		54HC								
				$T_A = -40$ to $85^\circ C$		$T_A = -55$ to $125^\circ C$								
				Typ	Guaranteed Limits									
V_{IH}	Minimum High Level Input Voltage		2.0V		1.5	1.5	1.5	V						
			4.5V		3.15	3.15	3.15	V						
			6.0V		4.2	4.2	4.2	V						
V_{IL}	Maximum Low Level Input Voltage**		2.0V		0.5	0.5	0.5	V						
			4.5V		1.35	1.35	1.35	V						
			6.0V		1.8	1.8	1.8	V						
V_{OH}	Minimum High Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 20 \mu A$	2.0V	2.0	1.9	1.9	1.9	V						
			4.5V	4.5	4.4	4.4	4.4	V						
			6.0V	6.0	5.9	5.9	5.9	V						
		4.5V	4.2	3.98	3.84	3.7	3.7	V						
									6.0V	5.7	5.48	5.34	5.2	V
V_{OL}	Maximum Low Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 20 \mu A$	2.0V	0	0.1	0.1	0.1	V						
			4.5V	0	0.1	0.1	0.1	V						
			6.0V	0	0.1	0.1	0.1	V						
		4.5V	0.2	0.26	0.33	0.4	0.4	V						
									6.0V	0.2	0.26	0.33	0.4	V
I_{IN}	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		± 0.1	± 1.0	± 1.0	μA						
I_{OZ}	Maximum TRI-STATE Leakage Current	Strobe = V_{CC} $V_{OUT} = V_{CC}$ or GND	6.0V		± 0.5	± 5	± 10	μA						
I_{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		8.0	80	160	μA						

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V $\pm 10\%$ the worst case output voltages (V_{OH} and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at $V_{CC} = 5.5V$ and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN} , I_{CC} , and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

** V_{IL} limits are currently tested at 20% of V_{CC} . The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics $V_{CC}=5V, T_A=25^{\circ}C, C_L=15\text{ pF}, t_r=t_f=6\text{ ns}$

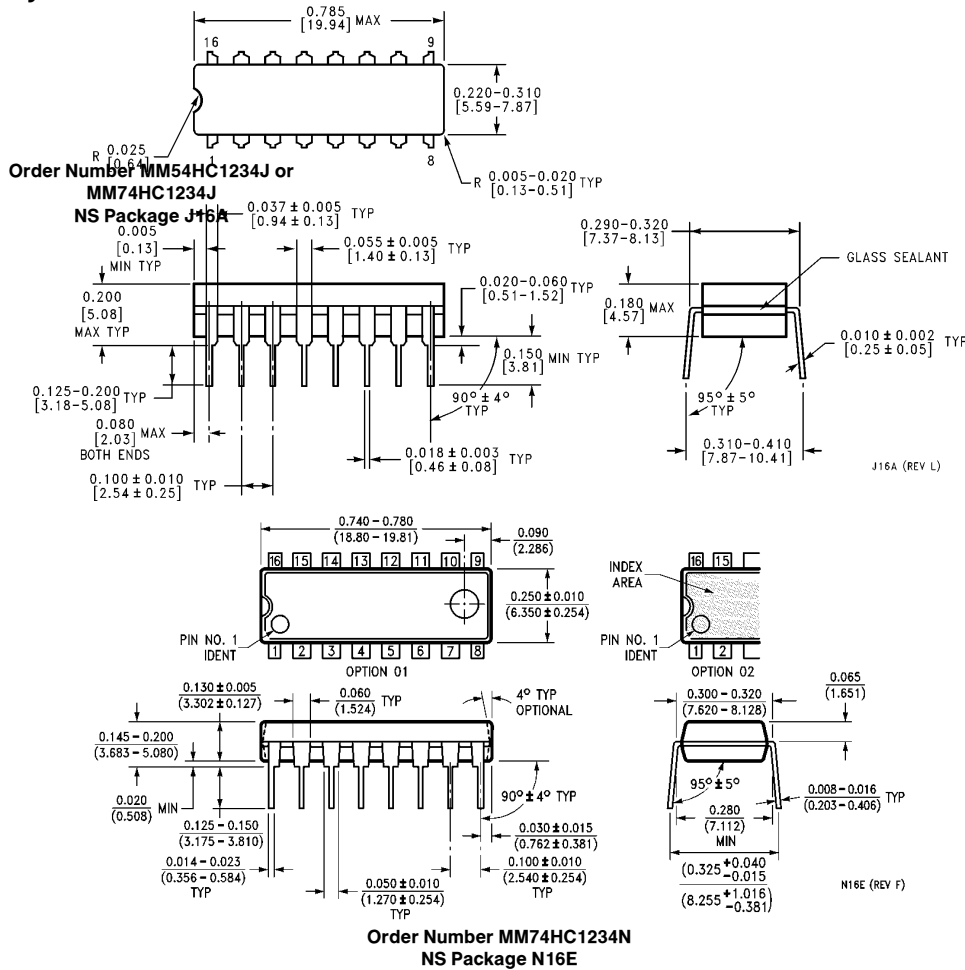
Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL}, t_{PLH}	Maximum Propagation Delay A, B or C to Y		26	35	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, A, B or C to W		27	35	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Any D to Y		22	29	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Any D to W		24	32	ns
t_{PZH}, t_{PZL}	Maximum Output Enable Time, W Output	$R_L=1\text{ k}\Omega$ $C_L=50\text{ pF}$	19	27	ns
t_{PZH}, t_{PZL}	Maximum Output Enable Time, Y Output	$R_L=1\text{ k}\Omega$ $C_L=50\text{ pF}$	19	26	ns
t_{PHZ}, t_{PLZ}	Maximum Output Disable Time W Output	$R_L=1\text{ k}\Omega$ $C_L=5\text{ pF}$	26	40	ns
t_{PHZ}, t_{PLZ}	Maximum Output Disable Time Y Output	$R_L=1\text{ k}\Omega$ $C_L=5\text{ pF}$	27	35	ns

AC Electrical Characteristics $C_L=50\text{ pF}, t_r=t_f=6\text{ ns}$ (unless otherwise specified)

Symbol	Parameter	Conditions	V_{CC}	$T_A=25^{\circ}C$		74HC $T_A=-40\text{ to }85^{\circ}C$		54HC $T_A=-55\text{ to }125^{\circ}C$		Units
				Typ	Guaranteed Limits					
t_{PHL}, t_{PLH}	Maximum Propagation Delay A, B or C to Y		2.0V	90	205	256		300		ns
			4.5V	31	41	51		60		
			6.0V	26	35	44		51		
t_{PHL}, t_{PLH}	Maximum Propagation Delay, A, B or C to W		2.0V	95	205	256		300		ns
			4.5V	32	41	51		60		
			6.0V	27	35	44		51		
t_{PHL}, t_{PLH}	Maximum Propagation Delay, any D to Y		2.0V	70	195	244		283		ns
			4.5V	27	39	49		57		
			6.0V	23	33	41		48		
t_{PHL}, t_{PLH}	Maximum Propagation Delay, any D to W		2.0V	75	185	231		268		ns
			4.5V	29	37	46		54		
			6.0V	25	32	40		46		
t_{PZH}, t_{PZL}	Maximum Output Enable Time W Output	$R_L=1\text{ k}\Omega$	2.0V	45	150	188		218		ns
			4.5V	21	30	38		44		
			6.0V	18	26	33		38		
t_{PZH}, t_{PZL}	Maximum Output Enable Time Y Output	$R_L=1\text{ k}\Omega$	2.0V	45	145	181		210		ns
			4.5V	21	29	36		42		
			6.0V	18	25	31		36		
t_{PHZ}, t_{PLZ}	Maximum Output Disable Time W Output	$R_L=1\text{ k}\Omega$	2.0V	60	220	275		319		ns
			4.5V	29	44	55		64		
			6.0V	25	37	46		54		
t_{PHZ}, t_{PLZ}	Maximum Output Disable Time Y Output	$R_L=1\text{ k}\Omega$	2.0V	60	195	244		283		ns
			4.5V	30	39	49		57		
			6.0V	26	33	41		48		
t_{THL}, t_{TLH}	Maximum Output Rise and Fall Time		2.0V	30	75	95		110		ns
			4.5V	8	15	19		22		
			6.0V	7	13	16		19		
C_{PD}	Power Dissipation Capacitance (Note 5)	(per package)		110					μF	
C_{IN}	Maximum Input Capacitance			5	10	10		10		μF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D=C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S=C_{PD} V_{CC} f + I_{CC}$.

Physical Dimensions inches (millimeters)



LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



National Semiconductor Corporation
 1111 West Bardin Road
 Arlington, TX 76017
 Tel: (800) 272-9959
 Fax: (800) 737-7018

National Semiconductor Europe
 Fax: (+49) 0-180-530 85 86
 Email: cnjwge@tevm2.nsc.com
 Deutsch Tel: (+49) 0-180-530 85 85
 English Tel: (+49) 0-180-532 78 32
 Français Tel: (+49) 0-180-532 93 58
 Italiano Tel: (+49) 0-180-534 16 80

National Semiconductor Hong Kong Ltd.
 19th Floor, Straight Block,
 Ocean Centre, 5 Canton Rd.
 Tsimshatsui, Kowloon
 Hong Kong
 Tel: (852) 2737-1600
 Fax: (852) 2736-9960

National Semiconductor Japan Ltd.
 Tel: 81-043-299-2309
 Fax: 81-043-299-2408

National does not assume any responsibility for use of any circuitry described, no circuit patent licenses are implied and National reserves the right at any time without notice to change said circuitry and specifications.

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.